

【ABSTRACT】

The present invention provides a method for doping carbon in a thin film on a wafer, the method comprising the steps of: arranging a thin film-formed wafer in a processing area; supplying an atmospheric gas into the processing area to bring the pressure in the processing area to a process pressure higher than atmospheric pressure; heating the processing area to bring the temperature in the processing area to a processing temperature; and supplying a source gas containing carbon to the processing area to allow the source gas to undergo a chemical reaction with the thin film under the process pressure at the process temperature, thereby injecting the carbon into the thin film.

[FIG. 3]